

NVGS5120P

Product Preview

Power MOSFET

-60 V, -3.0 A, Single P-Channel, TSOP-6

Features

- 60 V BVds, Low R_{DS(on)} in TSOP-6 Package
- 4.5 V Gate Rating
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR-Free and are RoHS Compliant

Applications

- High Side Load Switch
- Power Switch for Printers, Communication Equipment

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V _{DSS}	-60	V	
Gate-to-Source Voltage		V _{GS}	±20	V	
Continuous Drain Current (Note 1)	Steady State	I _D	T _A = 25°C	-2.6	A
			T _A = 85°C	-2.1	
	t ≤ 5 s	T _A = 25°C	-3.0		
Power Dissipation (Note 1)	Steady State	P _D	T _A = 25°C	1.5	W
	t ≤ 5 s			1.9	
Continuous Drain Current (Note 2)	Steady State	I _D	T _A = 25°C	-1.9	A
			T _A = 85°C	-1.5	
Power Dissipation (Note 2)	Steady State	P _D	T _A = 25°C	0.8	W
Pulsed Drain Current	t _p = 10 μs	I _{DM}	-11	A	
Operating Junction and Storage Temperature		T _J , T _{STG}	-55 to 175	°C	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T _L	260	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Ambient - Steady State (Note 1)	R _{θJA}	102	°C/W
Junction-to-Ambient - t = 5 s (Note 1)	R _{θJA}	77.6	
Junction-to-Ambient - Steady State (Note 2)	R _{θJA}	200	

1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces)
2. Surface-mounted on FR4 board using the minimum recommended pad size.

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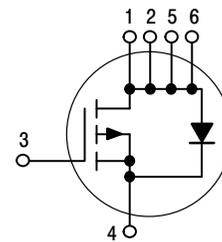


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V _{(BR)DSS}	R _{DS(ON)} MAX	I _D MAX
-60 V	111 mΩ @ -10 V	-3.0 A
	142 mΩ @ -4.5 V	

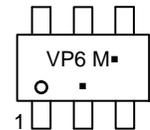
P-Channel



MARKING DIAGRAM

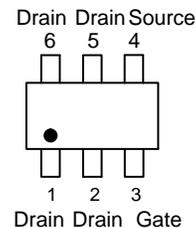


TSOP-6
CASE 318G
STYLE 1



VP6 = Device Code
M = Date Code
■ = Pb-Free Package
(Note: Microdot may be in either location)

PIN ASSIGNMENT



ORDERING INFORMATION

Device	Package	Shipping†
NVGS5120PT1G	TSOP-6 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = -250 μA	-60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = -48 V	T _J = 25°C		-1.0	μA
			T _J = 125°C		-5.0	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±12 V			± 100	nA
		V _{DS} = 0 V, V _{GS} = ±20 V			± 200	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = -250 μA	-1.0		-3.0	V
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = -10 V, I _D = -2.9 A		72	111	mΩ
		V _{GS} = -4.5 V, I _D = -2.5 A		88	142	
Forward Transconductance	g _{FS}	V _{DS} = -5.0 V, I _D = -6.0 A		10.1		S

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = -30 V		942		pF
Output Capacitance	C _{OSS}			72		
Reverse Transfer Capacitance	C _{RSS}			48		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = -10 V, V _{DS} = -30 V; I _D = -2.9 A		18.1		nC
Threshold Gate Charge	Q _{G(TH)}			1.2		
Gate-to-Source Charge	Q _{GS}			2.7		
Gate-to-Drain Charge	Q _{GD}			3.6		

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = -10 V, V _{DS} = -30 V, I _D = -1.0 A, R _G = 6.0 Ω		8.7		ns
Rise Time	t _r			4.9		
Turn-Off Delay Time	t _{d(OFF)}			38		
Fall Time	t _f			12.8		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = -0.9 A	T _J = 25°C		-0.75	-1.0	V
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = -0.9 A			18.3		ns
Charge Time	t _a				15.5		ns
Reverse Recovery Charge	Q _{RR}				15.1		nC

- Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%
- Switching characteristics are independent of operating junction temperatures

TYPICAL CHARACTERISTICS

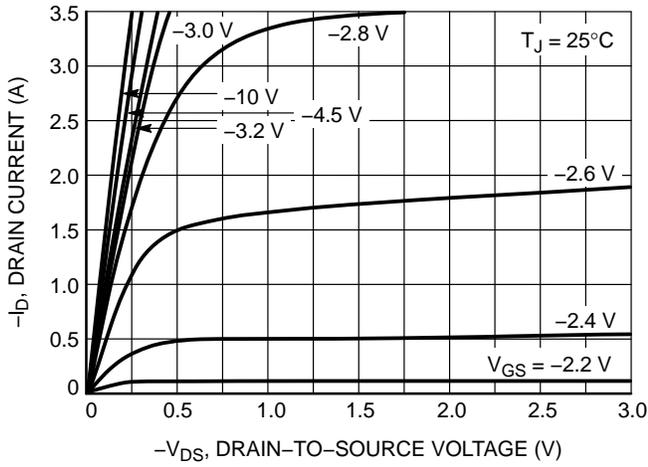


Figure 1. On-Region Characteristics

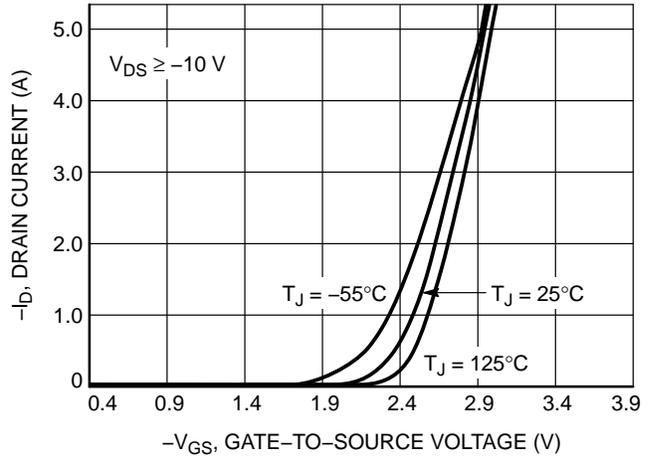


Figure 2. Transfer Characteristics

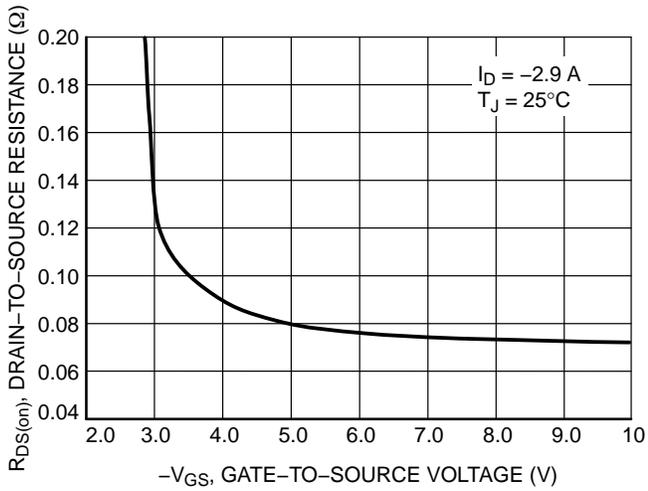


Figure 3. On-Resistance vs. Gate Voltage

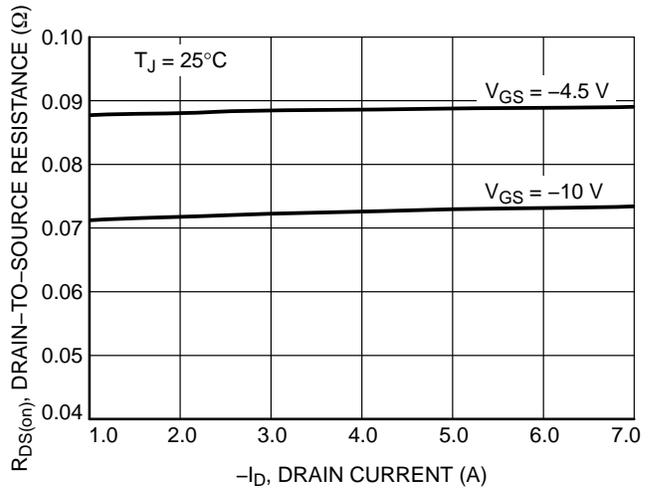


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

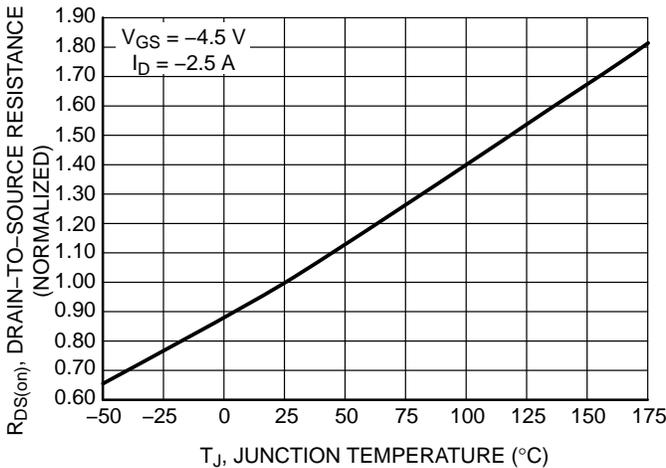


Figure 5. On-Resistance Variation with Temperature

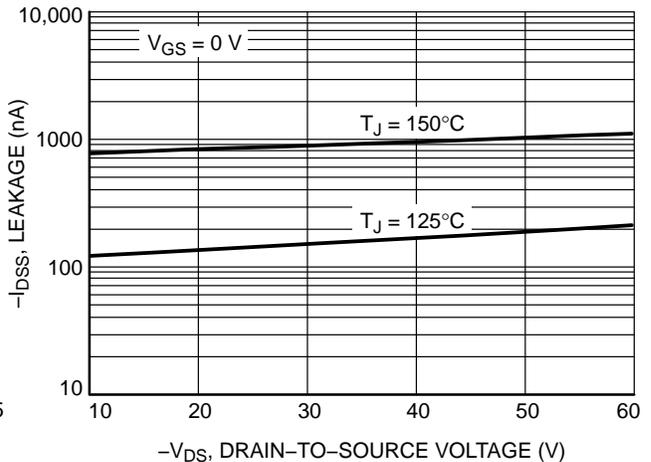


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

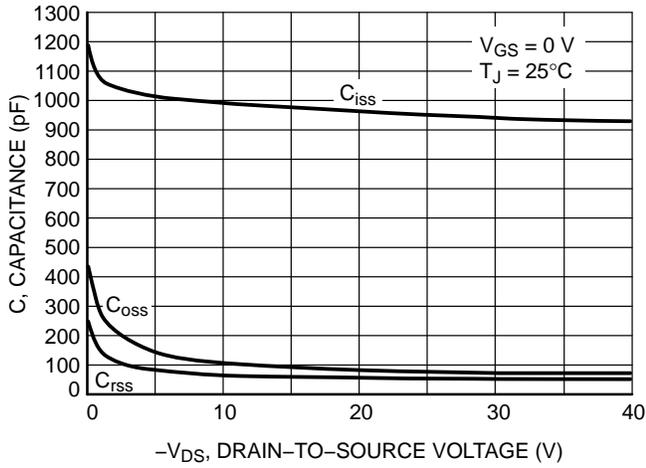


Figure 7. Capacitance Variation

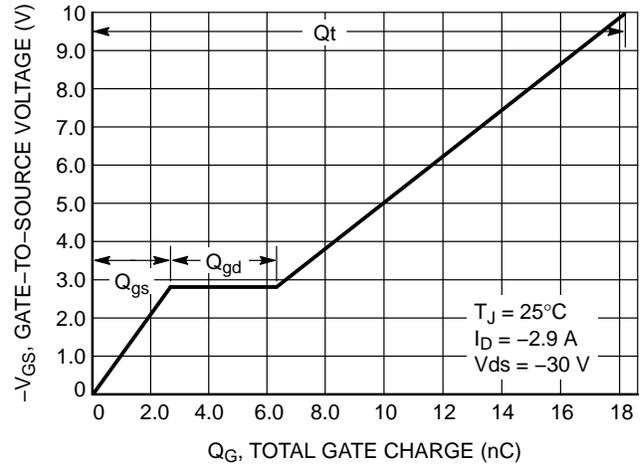


Figure 8. Gate-to-Source Voltage vs. Total Charge

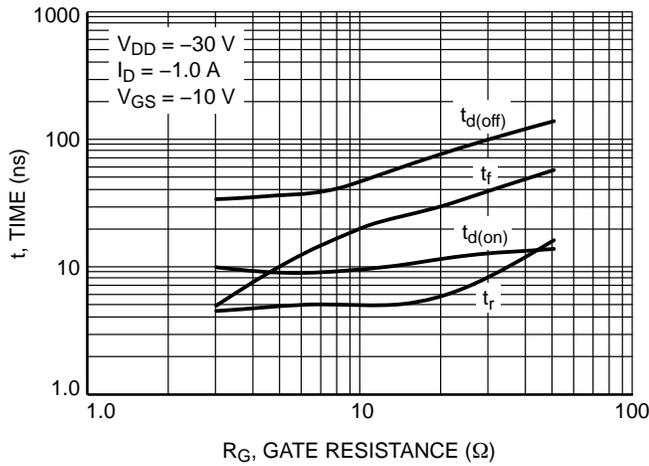


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

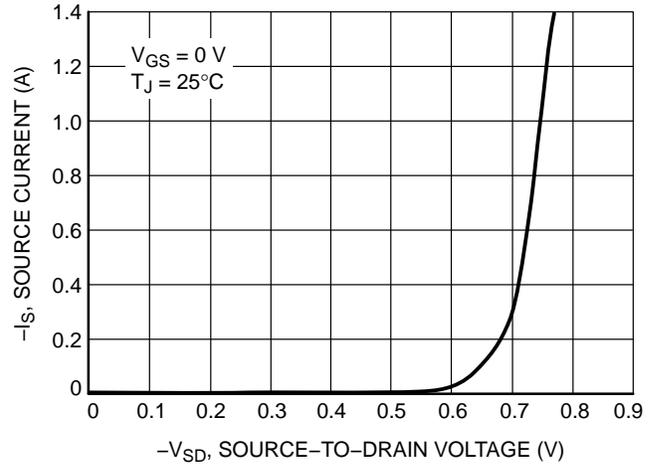
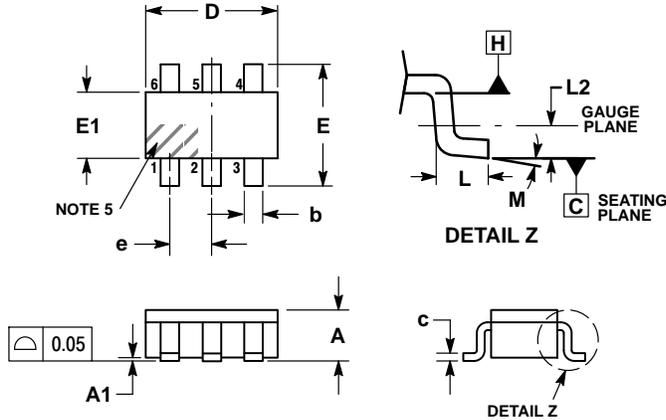


Figure 10. Diode Forward Voltage vs. Current

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PACKAGE DIMENSIONS

TSOP-6 CASE 318G-02 ISSUE V



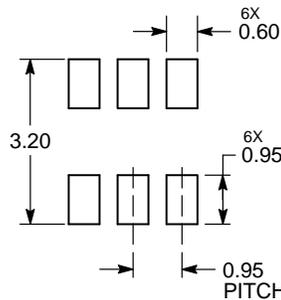
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
5. PIN ONE INDICATOR MUST BE LOCATED IN THE INDICATED ZONE.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.01	0.06	0.10
b	0.25	0.38	0.50
c	0.10	0.18	0.26
D	2.90	3.00	3.10
E	2.50	2.75	3.00
E1	1.30	1.50	1.70
e	0.85	0.95	1.05
L	0.20	0.40	0.60
L2	0.25 BSC		
M	0°	-	10°

- STYLE 1:
 PIN 1: DRAIN
 2: DRAIN
 3: GATE
 4: SOURCE
 5: DRAIN
 6: DRAIN

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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